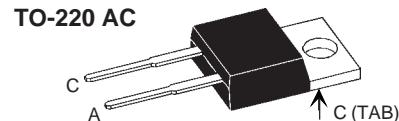
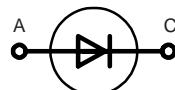


Power Schottky Rectifier

I_{FAV} = 10 A
V_{RRM} = 45 V
V_F = 0.46 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSS 10-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAV}	T _C = 135°C; rectangular, d = 0.5	10	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	160	A
E _{AS}	I _{AS} = 13 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	24	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.3	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	75	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	5 50	mA mA
V _F	I _F = 10 A; T _{VJ} = 125°C I _F = 10 A; T _{VJ} = 25°C I _F = 20 A; T _{VJ} = 125°C	0.46 0.51 0.64	V V V
R _{thJC} R _{thCH}		0.5	1.7 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

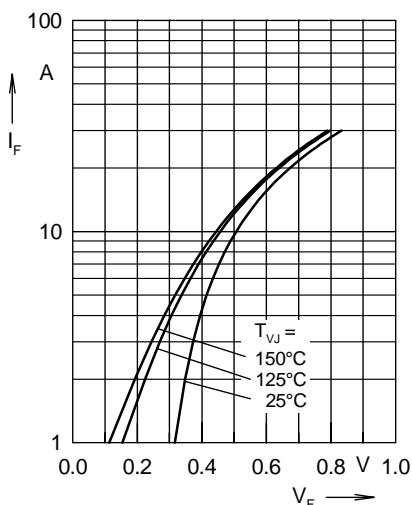


Fig. 1 Maximum forward voltage drop characteristics

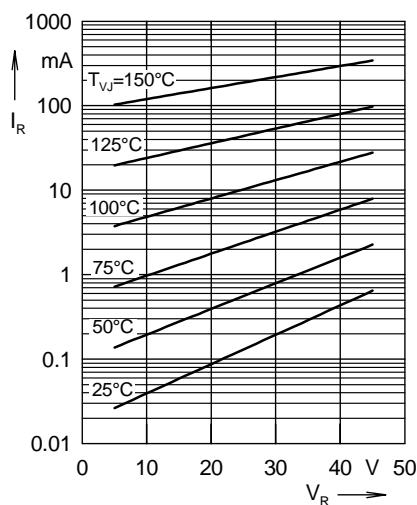


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

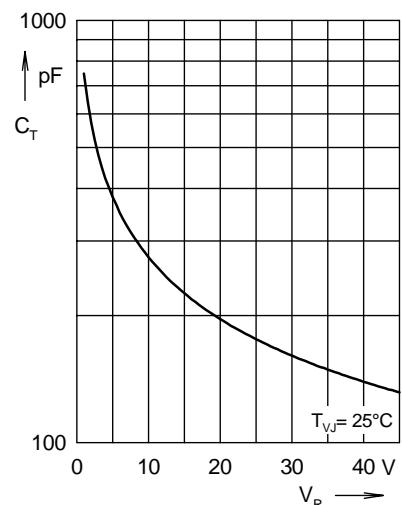


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

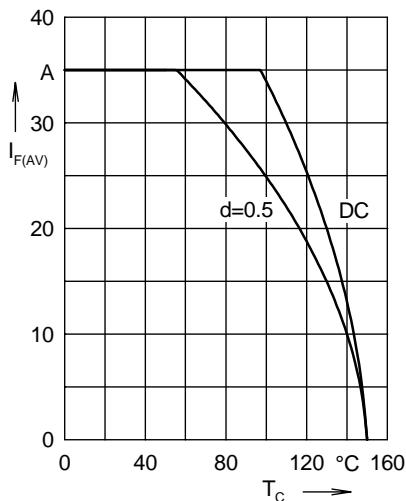


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

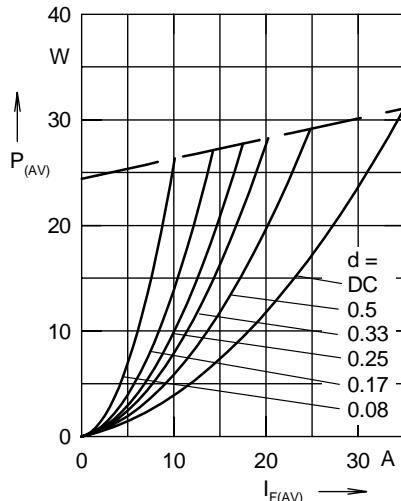


Fig. 5 Forward power loss characteristics

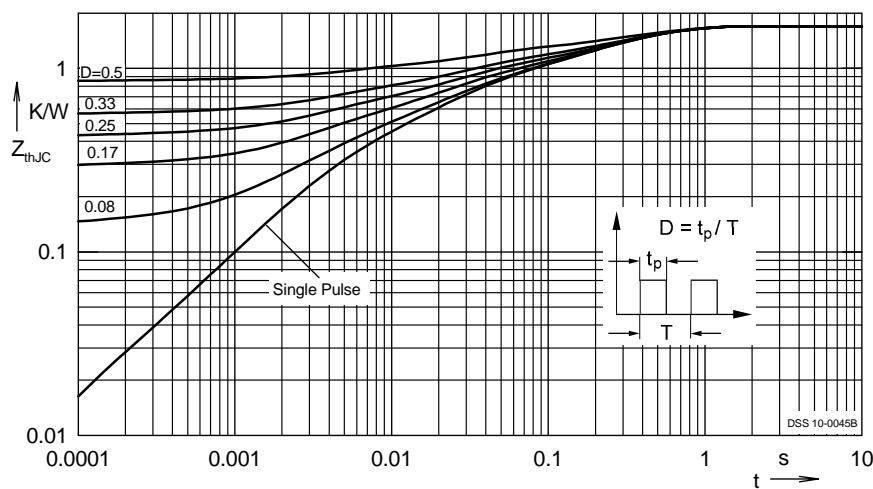


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode